

# ON Semiconductor

## Is Now

# onsemi™

To learn more about onsemi™, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

---

**onsemi** and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.



## ADP3414

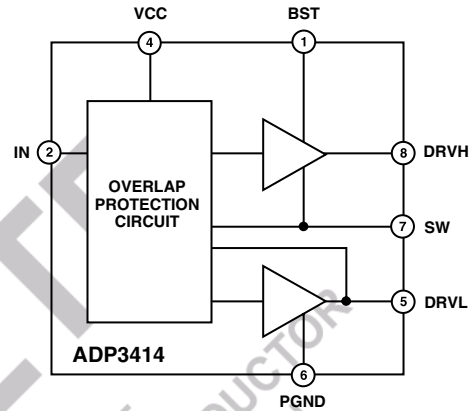
### FEATURES

- All-In-One Synchronous Buck Driver
- Bootstrapped High Side Drive
- One PWM Signal Generates Both Drives
- Anticross-Conduction Protection Circuitry
- Pulse-by-Pulse Disable Control

### APPLICATIONS

- Mobile Computing CPU Core Power Converters
- Multiphase Desktop CPU Supplies
- Single-Supply Synchronous Buck Converters
- Standard-to-Synchronous Converter Adaptations

### FUNCTIONAL BLOCK DIAGRAM



### GENERAL DESCRIPTION

The ADP3414 is a dual MOSFET driver optimized for driving two N-channel MOSFETs which are the two switches in a nonisolated synchronous buck power converter. Each of the drivers is capable of driving a 3000 pF load with a 20 ns propagation delay and a 30 ns transition time. One of the drivers can be bootstrapped and is designed to handle the high voltage slew rate associated with “floating” high side gate drivers. The ADP3414 includes overlapping drive protection (ODP) to prevent shoot-through current in the external MOSFETs.

The ADP3414 is specified over the commercial temperature range of 0°C to 70°C and is available in an 8-lead SOIC package.

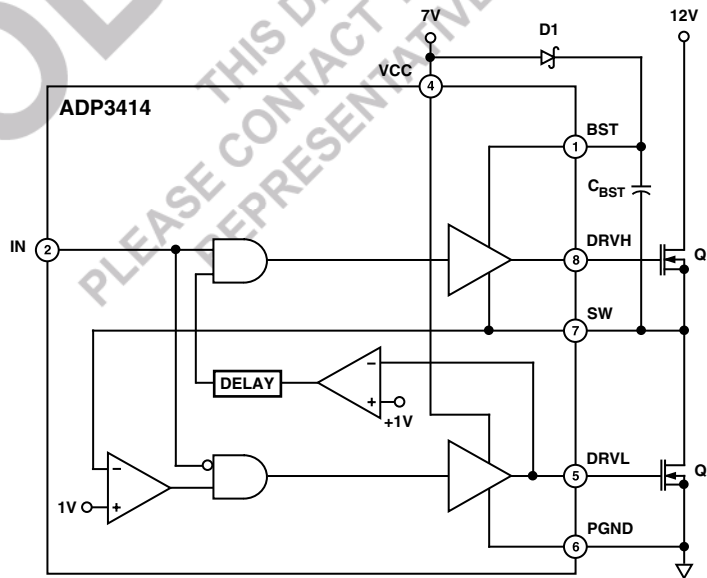


Figure 1. General Application Circuit

# ADP3414—SPECIFICATIONS<sup>1</sup> (T<sub>A</sub> = 0°C to 70°C, VCC = 7 V, BST = 4 V to 26 V, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>SUPPLY</b>						
Supply Voltage Range	VCC		4.15		7.5	V
Quiescent Current	ICC <sub>Q</sub>			1	2	mA
<b>PWM INPUT</b>						
Input Voltage High <sup>2</sup>			2.3			V
Input Voltage Low <sup>2</sup>					0.8	V
<b>HIGH SIDE DRIVER</b>						
Output Resistance, Sourcing Current		V <sub>BST</sub> - V <sub>SW</sub> = 5 V		3.0	5.0	Ω
		V <sub>BST</sub> - V <sub>SW</sub> = 7 V		2.0	3.5	Ω
Output Resistance, Sinking Current		V <sub>BST</sub> - V <sub>SW</sub> = 5 V		1.25	2.5	Ω
		V <sub>BST</sub> - V <sub>SW</sub> = 7 V		1.0	2.5	Ω
Transition Times <sup>3</sup> (See Figure 2)	t <sub>rDRVH</sub>	V <sub>BST</sub> - V <sub>SW</sub> = 7 V, C <sub>LOAD</sub> = 3 nF		36	47	ns
	t <sub>fDRVH</sub>	V <sub>BST</sub> - V <sub>SW</sub> = 7 V, C <sub>LOAD</sub> = 3 nF		20	30	ns
Propagation Delay <sup>3, 4</sup> (See Figure 2)	tpdh <sub>DRVH</sub>	V <sub>BST</sub> - V <sub>SW</sub> = 7 V		65	86	ns
	tpdl <sub>DRVH</sub>	V <sub>BST</sub> - V <sub>SW</sub> = 7 V		21	32	ns
<b>LOW SIDE DRIVER</b>						
Output Resistance, Sourcing Current		VCC = 5 V		3.0	5.0	Ω
		VCC = 7 V		2.0	3.5	Ω
Output Resistance, Sinking Current		VCC = 5 V		1.5	3.0	Ω
		VCC = 7 V		1.0	2.5	Ω
Transition Times <sup>3</sup> (See Figure 2)	t <sub>rDRVL</sub>	VCC = 7 V, C <sub>LOAD</sub> = 3 nF		27	35	ns
	t <sub>fDRVL</sub>	VCC = 7 V, C <sub>LOAD</sub> = 3 nF		19	26	ns
Propagation Delay <sup>3, 4</sup> (See Figure 2)	tpdh <sub>DRVL</sub>	VCC = 7 V		30	35	ns
	tpdl <sub>DRVL</sub>	VCC = 7 V		15	25	ns

## NOTES

<sup>1</sup>All limits at temperature extremes are guaranteed via correlation using standard Statistical Quality Control (SQC) methods.

<sup>2</sup>Logic inputs meet typical CMOS I/O conditions for source/sink current (~1 μA).

<sup>3</sup>AC specifications are guaranteed by characterization but not production tested.

<sup>4</sup>For propagation delays, “tpdh” refers to the specified signal going high; “tpdl” refers to it going low.

Specifications subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS\*

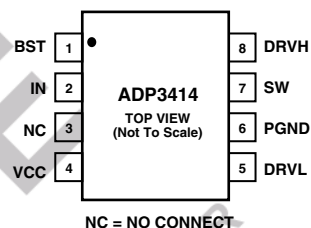
VCC	.....	-0.3 V to +8 V
BST	.....	-0.3 V to +30 V
BST to SW	.....	-0.3 V to +8 V
SW	.....	-5.0 V to +25 V
IN	.....	-0.3 V to VCC + 0.3 V
Operating Ambient Temperature Range	.....	0°C to 70°C
Operating Junction Temperature Range	.....	0°C to 125°C
$\theta_{JA}$	.....	155°C/W
$\theta_{JC}$	.....	40°C/W
Storage Temperature Range	.....	-65°C to +150°C
Lead Temperature (Soldering, 10 sec)	.....	300°C

\*This is a stress rating only; operation beyond these limits can cause the device to be permanently damaged. Unless otherwise specified, all voltages are referenced to PGND.

## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADP3414JR	0°C to 70°C	8-Lead Standard Small Outline (SOIC)	SOIC-8

## PIN CONFIGURATION



## PIN FUNCTION DESCRIPTIONS

Pin	Mnemonic	Function
1	BST	Floating Bootstrap Supply for the Upper MOSFET. A capacitor connected between BST and SW Pins holds this bootstrapped voltage for the high side MOSFET as it is switched. The capacitor should be chosen between 100 nF and 1 $\mu$ F.
2	IN	TTL-level input signal that has primary control of the drive outputs.
3	NC	No Connection
4	VCC	Input Supply. This pin should be bypassed to PGND with $\sim$ 1 $\mu$ F ceramic capacitor.
5	DRVL	Synchronous Rectifier Drive. Output drive for the lower (synchronous rectifier) MOSFET.
6	PGND	Power Ground. Should be closely connected to the source of the lower MOSFET.
7	SW	This pin is connected to the buck-switching node, close to the upper MOSFET's source. It is the floating return for the upper MOSFET drive signal. It is also used to monitor the switched voltage to prevent turn-on of the lower MOSFET until the voltage is below $\sim$ 1 V. Thus, according to operating conditions, the high low transition delay is determined at this pin.
8	DRVH	Buck Drive. Output drive for the upper (buck) MOSFET.

## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADP3414 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



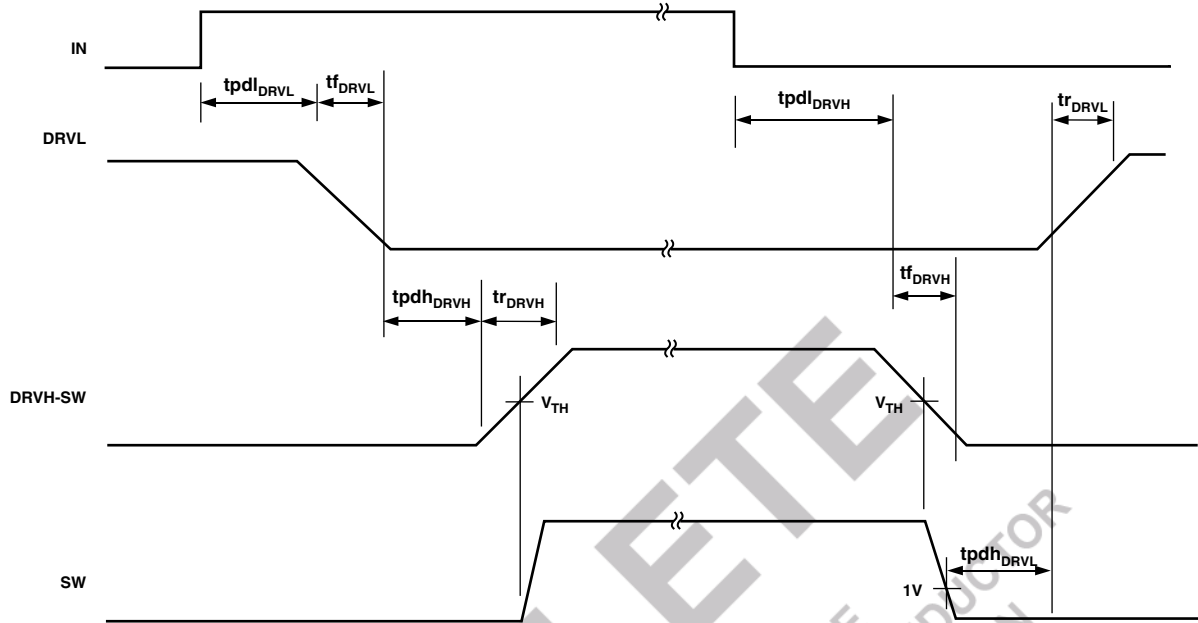
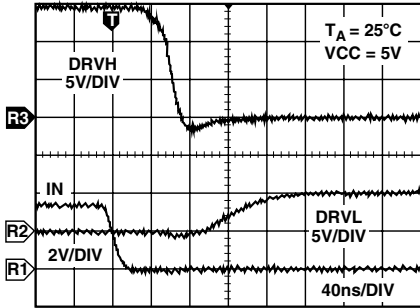


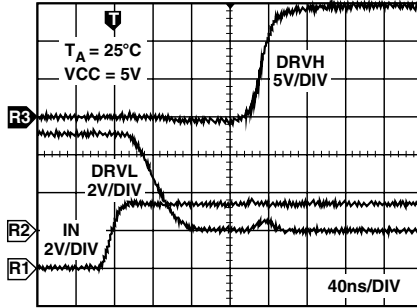
Figure 2. Nonoverlap Timing Diagram (Timing Is Referenced to the 90% and 10% Points Unless Otherwise Noted)

OBSOLETE  
 THIS DEVICE IS OBSOLETE  
 PLEASE CONTACT YOUR ON SEMICONDUCTOR  
 REPRESENTATIVE FOR INFORMATION

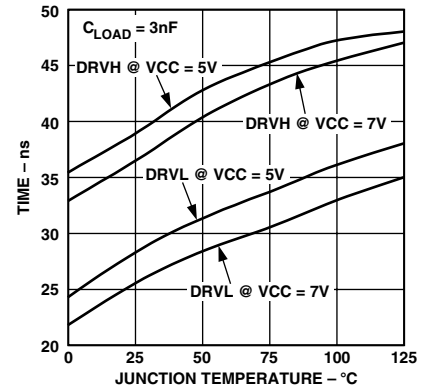
# Typical Performance Characteristics—ADP3414



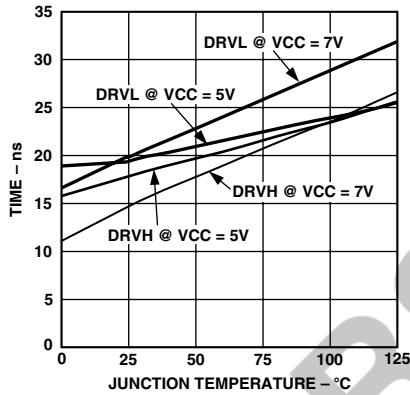
TPC 1. DRVH Fall and DRVL Rise Times



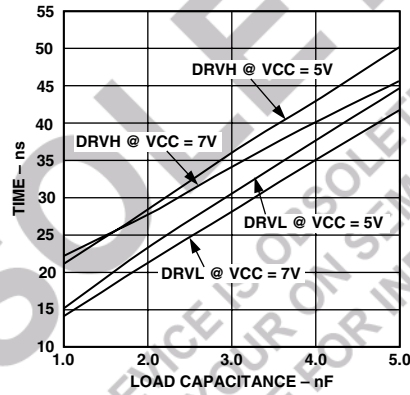
TPC 2. DRVL Fall and DRVH Rise Times



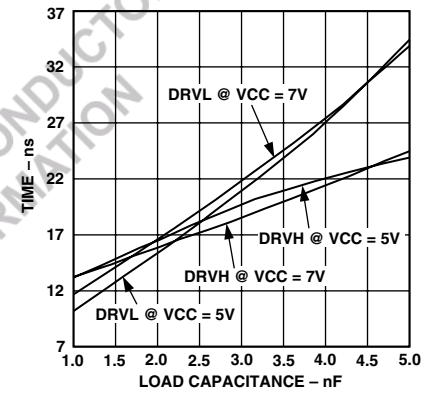
TPC 3. DRVH and DRVL Rise Times vs. Temperature



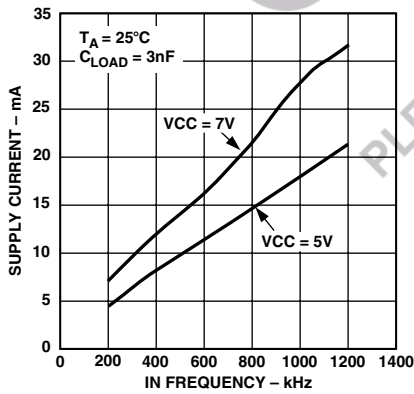
TPC 4. DRVH and DRVL Fall Times vs. Temperature



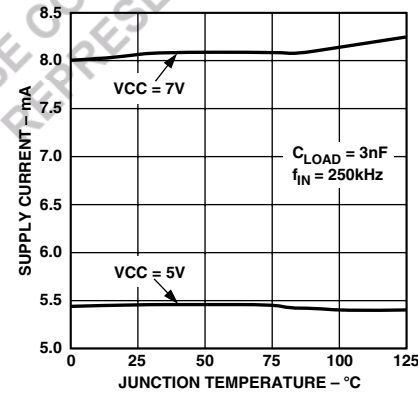
TPC 5. DRVH and DRVL Rise Times vs. Load Capacitance



TPC 6. DRVH and DRVL Fall Times vs. Load Capacitance



TPC 7. Supply Current vs. Frequency



TPC 8. Supply Current vs. Temperature

# ADP3414

## THEORY OF OPERATION

The ADP3414 is a dual MOSFET driver optimized for driving two N-channel MOSFETs in a synchronous buck converter topology. A single PWM input signal is all that is required to properly drive the high side and the low side FETs. Each driver is capable of driving a 3 nF load.

A more detailed description of the ADP3414 and its features follows. Refer to the Functional Block Diagram.

### Low Side Driver

The low side driver is designed to drive low  $R_{DS(ON)}$  N-channel MOSFETs. The maximum output resistance for the driver is 3.5  $\Omega$  for sourcing and 2.5  $\Omega$  for sinking gate current. The low output resistance allows the driver to have 20 ns rise and fall times into a 3 nF load. The bias to the low side driver is internally connected to the VCC supply and PGND.

When the driver is enabled, the driver's output is 180 degrees out of phase with the PWM input. When the ADP3414 is disabled, the low side gate is held low.

### High-Side Driver

The high side driver is designed to drive a floating low  $R_{DS(ON)}$  N-channel MOSFET. The maximum output resistance for the driver is 3.5  $\Omega$  for sourcing and 2.5  $\Omega$  for sinking gate current. The low output resistance allows the driver to have 30 ns rise and fall times into a 3 nF load. The bias voltage for the high side driver is developed by an external bootstrap supply circuit, which is connected between the BST and SW Pins.

The bootstrap circuit comprises a diode, D1, and bootstrap capacitor,  $C_{BST}$ . When the ADP3414 is starting up, the SW Pin is at ground, so the bootstrap capacitor will charge up to VCC through D1. When the PWM input goes high, the high side driver will begin to turn the high side MOSFET, Q1, ON by pulling charge out of  $C_{BST}$ . As Q1 turns ON, the SW Pin will rise up to  $V_{IN}$ , forcing the BST Pin to  $V_{IN} + V_{C(BST)}$ , which is enough gate to source voltage to hold Q1 ON. To complete the cycle, Q1 is switched OFF by pulling the gate down to the voltage at the SW Pin. When the low side MOSFET, Q2, turns ON, the SW Pin is pulled to ground. This allows the bootstrap capacitor to charge up to VCC again.

The high-side driver's output is in phase with the PWM input. When the driver is disabled, the high side gate is held low.

### Overlap Protection Circuit

The overlap protection circuit (OPC) prevents both of the main power switches, Q1 and Q2, from being ON at the same time. This is done to prevent shoot-through currents from flowing through both power switches and the associated losses that can occur during their ON-OFF transitions. The overlap protection circuit accomplishes this by adaptively controlling the delay from Q1's turn OFF to Q2's turn ON and by internally setting the delay from Q2's turn OFF to Q1's turn ON.

To prevent the overlap of the gate drives during Q1's turn OFF and Q2's turn ON, the overlap circuit monitors the voltage at the SW Pin. When the PWM input signal goes low, Q1 will begin to turn OFF (after a propagation delay), but before Q2 can turn ON, the overlap protection circuit waits for the voltage at the SW Pin to fall from  $V_{IN}$  to 1 V. Once the voltage on the SW Pin has fallen to 1 V, Q2 will begin turn ON. By waiting for the voltage on the SW Pin to reach 1 V, the overlap protection circuit ensures that Q1 is OFF before Q2 turns on, regardless of variations in temperature, supply voltage, gate charge, and drive current.

To prevent the overlap of the gate drives during Q2's turn OFF and Q1's turn ON, the overlap circuit provides a internal delay that is set to 50 ns. When the PWM input signal goes high, Q2 will begin to turn OFF (after a propagation delay), but before Q1 can turn ON, the overlap protection circuit waits for the voltage at DRV1 to drop to around 10% of VCC. Once the voltage at DRV1 has reached the 10% point, the overlap protection circuit will wait for a 20 ns typical propagation delay. Once the delay period has expired, Q1 will begin turn ON.

## APPLICATION INFORMATION

### Supply Capacitor Selection

For the supply input (VCC) of the ADP3414, a local bypass capacitor is recommended to reduce the noise and to supply some of the peak currents drawn. Use a 1  $\mu$ F, low ESR capacitor. Multilayer ceramic chip (MLCC) capacitors provide the best combination of low ESR and small size and can be obtained from the following vendors:

Murata	GRM235Y5V106Z16	www.murata.com
Taiyo-Yuden	EMK325F106ZF	www.t-yuden.com
Tokin	C23Y5V1C106ZP	www.tokin.com

Keep the ceramic capacitor as close as possible to the ADP3414.

### Bootstrap Circuit

The bootstrap circuit uses a charge storage capacitor ( $C_{BST}$ ) and a Schottky diode, as shown in Figure 1. Selection of these components can be done after the high side MOSFET has been chosen.

The bootstrap capacitor must have a voltage rating that is able to handle the maximum battery voltage plus 5 V. A minimum 50 V rating is recommended. The capacitance is determined using the following equation:

$$C_{BST} = \frac{Q_{GATE}}{\Delta V_{BST}}$$

where,  $Q_{GATE}$  is the total gate charge of the high side MOSFET, and  $\Delta V_{BST}$  is the voltage droop allowed on the high side MOSFET drive. For example, the IRF7811 has a total gate charge of about 20 nC. For an allowed droop of 200 mV, the required bootstrap capacitance is 100 nF. A good quality ceramic capacitor should be used.

A Schottky diode is recommended for the bootstrap diode due to its low forward drop, which maximizes the drive available for the high side MOSFET. The bootstrap diode must have a minimum 40 V rating to withstand the maximum battery voltage plus 5 V. The average forward current can be estimated by:

$$I_{F(AVG)} \approx Q_{GATE} \times f_{MAX}$$

where  $f_{MAX}$  is the maximum switching frequency of the controller. The peak surge current rating should be checked in-circuit, since this is dependent on the source impedance of the 5 V supply and the ESR of  $C_{BST}$ .



## Printed Circuit Board Layout Considerations

Use the following general guidelines when designing printed circuit boards:

1. Trace out the high current paths and use short, wide traces to make these connections.
2. Connect the PGND pin of the ADP3414 as close as possible to the source of the lower MOSFET.
3. The VCC bypass capacitor should be located as close as possible to VCC and PGND Pins.

## Typical Application Circuits

The circuit in Figure 3 shows how two drivers can be combined with the ADP3160 to form a total power conversion solution for  $V_{CC(CORE)}$  generation in a high current Intel CPU computer. Figure 4 gives a similar application circuit for a 45 A AMD processor.

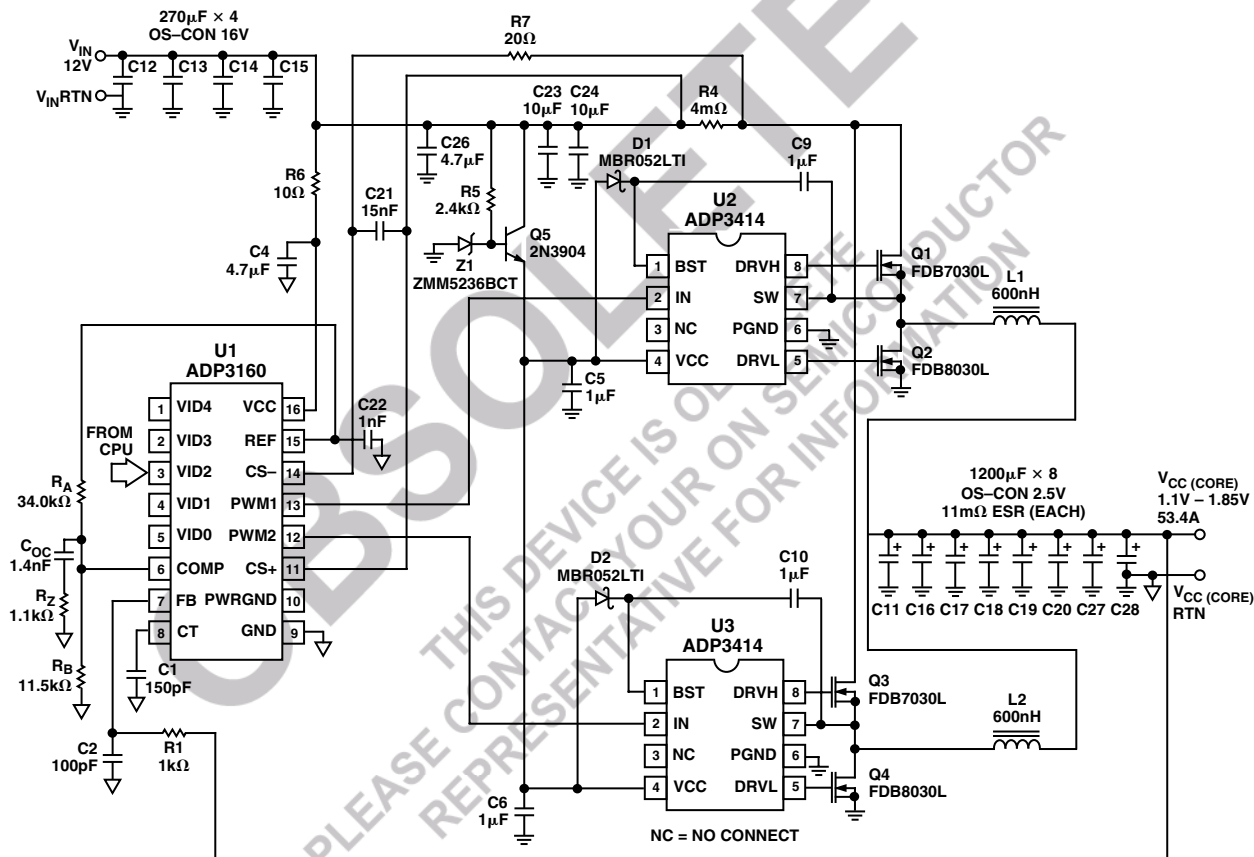


Figure 3. 53.4 A Intel CPU Supply Circuit



# ADP3414

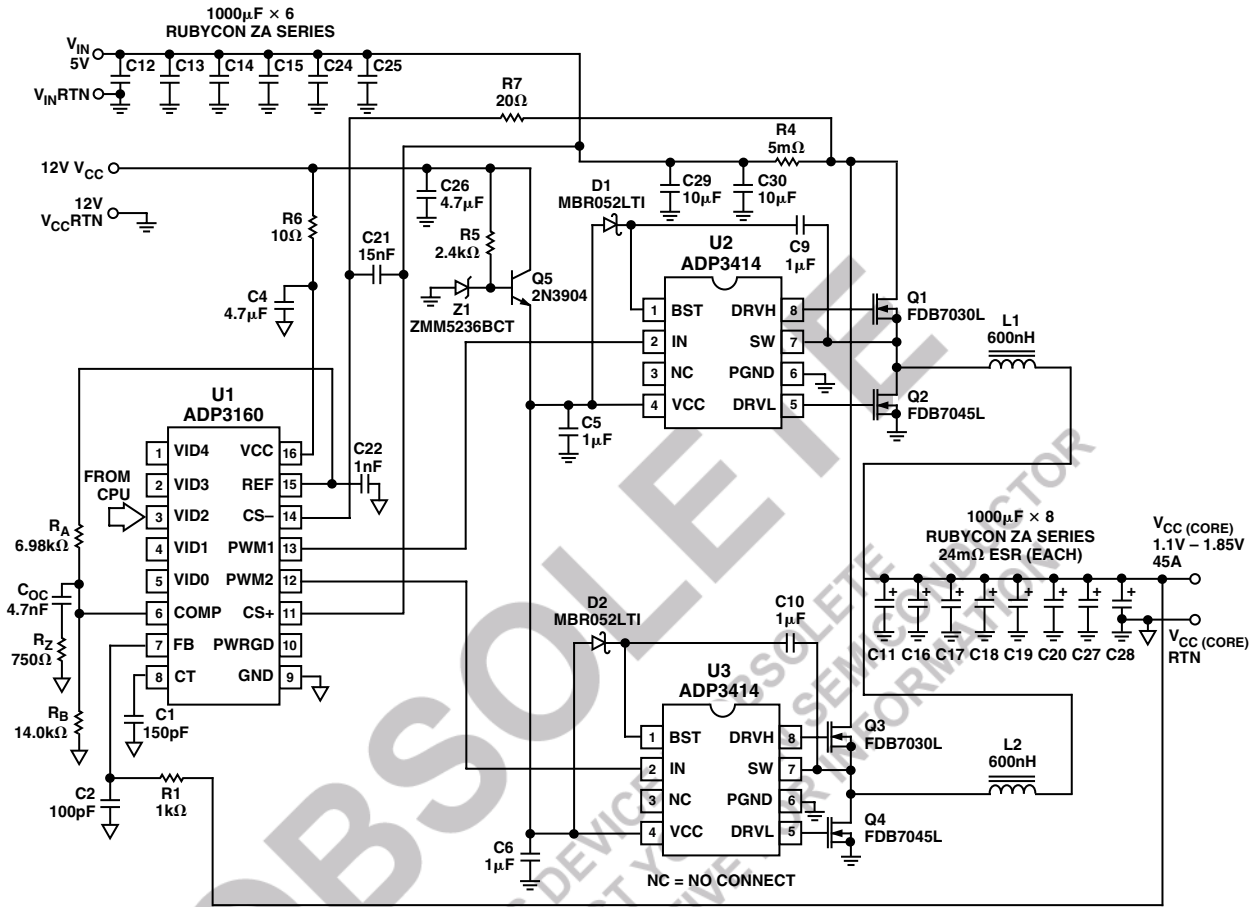
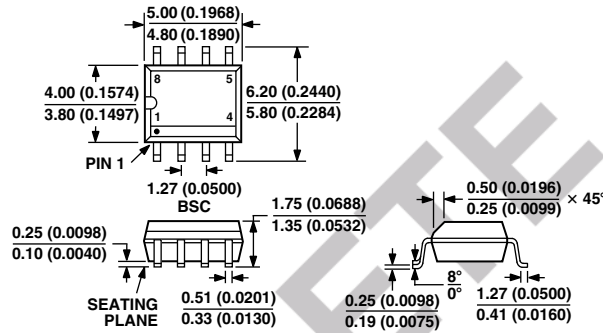


Figure 4. 45 A Athlon Duron CPU Supply Circuit

OUTLINE DIMENSIONS

8-Lead Standard Small Outline Package [SOIC]  
Narrow Body  
(R-8)

Dimensions shown in millimeters and (inches)



CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN  
COMPLIANT TO JEDEC STANDARDS MS-012AA

OBSOLETE

THIS DEVICE IS OBSOLETE IN SEMICONDUCTOR

PLEASE CONTACT YOUR ON SEMICONDUCTOR REPRESENTATIVE FOR INFORMATION

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
Email: [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

N. American Technical Support: 800-282-9855 Toll Free  
USA/Canada.

Europe, Middle East and Africa Technical Support:  
Phone: 421 33 790 2910

Japan Customer Focus Center  
Phone: 81-3-5773-3850

ON Semiconductor Website: [www.onsemi.com](http://www.onsemi.com)

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative